





100V NPN LOW SATURATION TRANSISTOR IN SOT23

Features

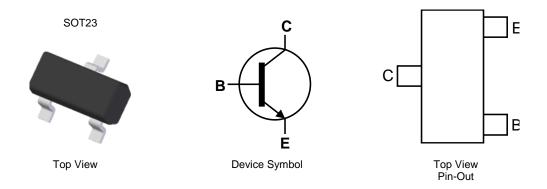
- BV_{CEO} > 100V
- BV_{CEX} > 170V Forward Blocking Voltage
- BV_{ECO} > 6V Reverse Blocking Voltage
- I_C = 3A high Continuous Collector Current
- Low Saturation Voltage, V_{CE(SAT)} < 80mV @1A
- R_{CE(SAT)} = 67mΩ for a Low Equivalent On-Resistance
- 1.25W Power Dissipation
- h_{FE} Specified up to 3A for High Current Gain Hold Up
- Complementary PNP Type: ZXTP25100BFH
- Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: SOT23
- Case Material: molded plastic, "Green" Molding Compound;
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 (3)
- Weight 0.008 grams (Approximate)

Applications

- Lamp Relay and Solenoid Drivers
- General Switching in Automotive and Industrial Applications
- Motor Drive and Control



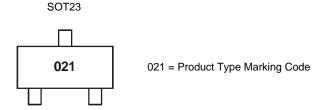
Ordering Information (Note 4)

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXTN25100BFHTA	021	7	8	3.000

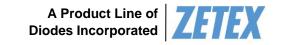
Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information







Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	170	V
Collector-Emitter Voltage (Forward Blocking)	V _{CEX}	170	V
Collector-Emitter Voltage	V _{CEO}	100	V
Emitter-Base Voltage (Reverse Blocking)	V _{ECO}	6	V
Emitter-Base Voltage	V _{EBO}	7	V
Continuous Collector Current	Ic	3	Α
Peak Pulse Current	I _{CM}	9	Α

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
	(Note 5)		0.60 4.80		
	(Note 6)		0.73 5.84		
Power Dissipation Linear Derating Factor	(Note 7)	P _D	1.05 8.4	W mW	
	(Note 8)		1.25 9.6		
	(Note 9)		1.81 14.5		
	(Note 5)		209		
	(Note 6)	1	171		
Thermal Resistance, Junction to Ambient	(Note 7)	R _{0JA}	119	°C/W	
	(Note 8)	1	100		
	(Note 9)	1	69		
Thermal Resistance, Junction to Leads (Note 10)		R _{0JL}	75	°C/W	
Operating and Storage Temperature Range	$T_{J_i}T_{STG}$	-55 to +150	°C		

ESD Ratings (Note 11)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	8,000	V	3B
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

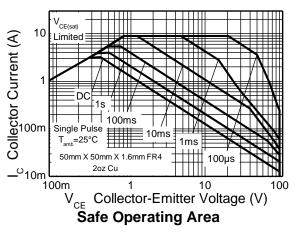
Notes:

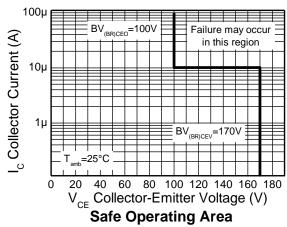
- 5. For a device mounted on minimum recommended pad layout with 1oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under
- still air conditions whilst operating in steady-state.

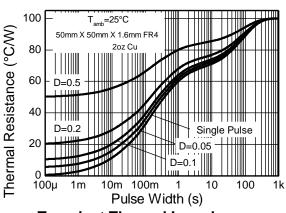
 6. Same as Note 5, except mounted with the collector lead on 15mm x 15mm 1oz copper.
- 7. Same as Note 5, except mounted with the collector lead on 25mm x 25mm 2oz copper. 8. Same as Note 5, except mounted with the collector lead on 50mm x 50mm 2 oz copper.
- 9. Same as Note 8, except measured at t < 5 seconds.
- 10. Thermal resistance from junction to solder-point (at the end of collector lead).
- 11.Refer to JEDEC specification JESD22-A114 and JESD22-A115.

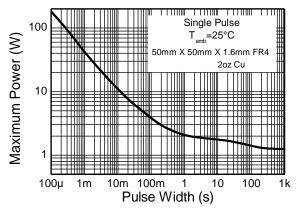


Thermal Characteristics and Derating information



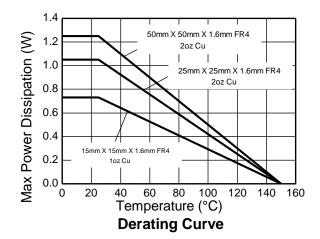




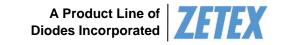


Transient Thermal Impedance

Pulse Power Dissipation







Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	170	220	-	V	$I_{C} = 100 \mu A$
Collector-Emitter Breakdown Voltage (Forward Blocking) (Note 12)	BV _{CEX}	170	210	-	V	$I_C = 100\mu A, R_{BE} < 1k\Omega \text{ or}$ -1V < $V_{BE} < 0.25V$
Collector-Emitter Breakdown Voltage (Note 12)	BV_CEO	100	120	-	V	$I_C = 1mA$
Emitter-Collector Breakdown Voltage (Reverse Blocking) (Note 12)	BV _{ECX}	6	7	-	V	I_E = 100μA, R_{BC} < 1k Ω or 0.25V > V_{BC} > -0.25V
Emitter-Collector Breakdown Voltage	BV_{ECO}	6	8.4	-	٧	$I_E = 100\mu A$
Emitter-Base Breakdown Voltage	BV_{EBO}	7	8	-	V	$I_E = 100\mu A$
Collector Cut-Off Current	I _{CBO}	-	<1	50 20	nA	V _{CB} = 136V V _{CB} = 136V, T _A = +100°C
Collector Emitter Cut-Off Current	I _{CEX}	-	-	100	nA	V_{CE} = 136V, R_{BE} < 1k Ω or -1V < V_{BE} < 0.25V
Emitter Cut-Off Current	I _{EBO}	-	<1	50	nA	$V_{EB} = 5.6V$
Static Forward Current Transfer Ratio (Note 12)	h _{FE}	100 50 -	200 85 20	300 - -	-	$I_C = 10 \text{mA}, V_{CE} = 2V$ $I_C = 1A, V_{CE} = 2V$ $I_C = 3A, V_{CE} = 2V$
Collector-Emitter Saturation Voltage (Note 12)	V _{CE(sat)}	- - -	40 100 70 200	55 135 80 250	mV	$I_C = 0.5A$, $I_B = 50mA$ $I_C = 0.5A$, $I_B = 10mA$ $I_C = 1A$, $I_B = 100mA$ $I_C = 3A$, $I_B = 300mA$
Base-Emitter Saturation Voltage (Note 12)	$V_{BE(sat)}$	-	940	1050	mV	$I_C = 3A$, $I_B = 300mA$
Base-Emitter Saturation Voltage (Note 12)	$V_{BE(on)}$	-	890	1000	mV	$I_C = 3A$, $V_{CE} = 2V$
Transition Frequency	f⊤	-	160	-	MHz	$I_C = 100 \text{mA}, V_{CE} = 5 \text{V},$ f = 100MHz
Collector Output Capacitance	C_{obo}	-	9.4	20	pF	$V_{CB} = 10V, f = 1MHz$
Delay Time	t _(d)	-	16	-	ns	
Rise Time	t _(r)	-	55	-	ns	$V_{CC} = 10V, I_C = 0.5A,$
Storage Time	t _(s)	-	677	-	ns	$I_{B1} = -I_{B2} = 50 \text{mA}$
Fall Time	t _(f)	-	95	-	ns	

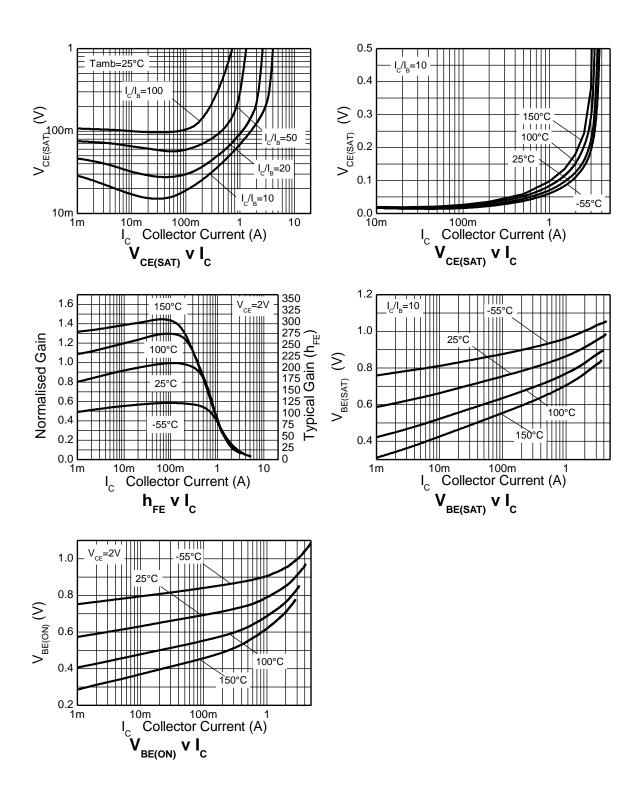
Note:

12. Measured under pulsed conditions. Pulse width ≤ 300µs. Duty cycle ≤ 2%





Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

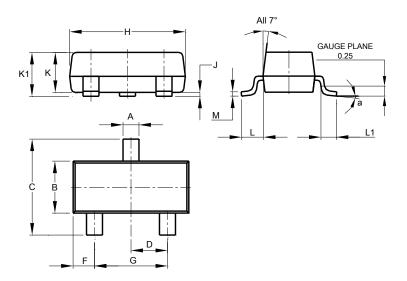






Package Outline Dimensions

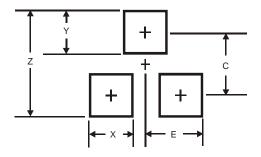
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



SOT23					
Dim	Min	Max	Тур		
Α	0.37	0.51	0.40		
В	1.20	1.40	1.30		
С	2.30	2.50	2.40		
D	0.89	1.03	0.915		
F	0.45	0.60	0.535		
G	1.78	2.05	1.83		
Н	2.80	3.00	2.90		
J	0.013	0.10	0.05		
K	0.890	1.00	0.975		
K1	0.903	1.10	1.025		
L	0.45	0.61	0.55		
L1	0.25	0.55	0.40		
М	0.085	0.150	0.110		
а	8°				
All	All Dimensions in mm				

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)		
Z	2.9		
Х	0.8		
Υ	0.9		
С	2.0		
Е	1.35		

Note: For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device terminals and PCB tracking.





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